

Shengdong Zhang

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Photoreactive and Metal-Platable Copolymer Inks for High-Throughput, Room-Temperature Printing of Flexible Metal Electrodes for Thin-Film Electronics. <i>Advanced Materials</i> , 2016, 28, 4926-4934.	11.1	77
2	Large-area patterning of full-color quantum dot arrays beyond 1000 pixels per inch by selective electrophoretic deposition. <i>Nature Communications</i> , 2021, 12, 4603.	5.8	64
3	Anodized ITO Thin-Film Transistors. <i>Advanced Functional Materials</i> , 2014, 24, 4170-4175.	7.8	41
4	Room-Temperature-Processed Flexible Amorphous InGaZnO Thin Film Transistor. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 25850-25857.	4.0	36
5	One Gate Diode-Connected Dual-Gate a-IGZO TFT Driven Pixel Circuit for Active Matrix Organic Light-Emitting Diode Displays. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 3800-3803.	1.6	34
6	Epsilon-near-zero medium for optical switches in a monolithic waveguide chip at 1.9 μm . <i>Nanophotonics</i> , 2018, 7, 1835-1843.	2.9	33
7	Metal Reaction-Induced Bulk-Doping Effect in Forming Conductive Source-Drain Regions of Self-Aligned Top-Gate Amorphous InGaZnO Thin-Film Transistors. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 11442-11448.	4.0	33
8	A Method to Reduce Forming Voltage Without Degrading Device Performance in Hafnium Oxide-Based 1T1R Resistive Random Access Memory. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 341-345.	1.2	29
9	Drain-Induced-Barrier-Lowering-Like Effect Induced by Oxygen-Vacancy in Scaling-Down via-Contact Type Amorphous InGaZnO Thin-Film Transistors. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 685-690.	1.2	21
10	Performance Enhancement and Bending Restoration for Flexible Amorphous Indium Gallium Zinc Oxide Thin-Film Transistors by Low-Temperature Supercritical Dehydration Treatment. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 8584-8594.	4.0	20
11	Solving the Scaling Issue of Increasing Forming Voltage in Resistive Random Access Memory Using High-k Spacer Structure. <i>Advanced Electronic Materials</i> , 2017, 3, 1700171.	2.6	19
12	Enhancing the Electrical Uniformity and Reliability of the HfO_2 -Based RRAM Using High-Permittivity Ta_2O_5 Side Wall. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 627-632.	1.2	17
13	A Back-Channel-Etched Amorphous InGaZnO Thin-Film Transistor Technology With Al-Doped ZnO as Source/Drain and Pixel Electrodes. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 2205-2209.	1.6	15
14	Implementation of Self-Aligned Top-Gate Amorphous Zinc Tin Oxide Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2019, 40, 901-904.	2.2	15
15	Performance and Stability Improvements of Back-Channel-Etched Amorphous Indium-Gallium-Zinc Thin-Film-Transistors by $\text{CF}_4 + \text{O}_2$ Plasma Treatment. <i>IEEE Electron Device Letters</i> , 2015, 36, 911-913.	2.2	14
16	Reduced graphene oxide-induced crystallization of CuPc interfacial layer for high performance of perovskite photodetectors. <i>RSC Advances</i> , 2019, 9, 3800-3808.	1.7	14
17	High-Performance Self-Aligned Top-Gate Amorphous InGaZnO TFTs With 4 nm-Thick Atomic-Layer-Deposited AlO_x Insulator. <i>IEEE Electron Device Letters</i> , 2022, 43, 729-732.	2.2	14
18	Nanocrystalline SnO_2 thin films prepared by anodization of sputtered Sn thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .	0.9	11

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19	Pâ€20: Effects of N₂O Plasma Treatment Time on the Performance of Selfâ€Aligned Topâ€Gate amorphous oxide Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2017, 48, 1299-1302.	0.1	11
20	Abnormal Bias Instabilities Induced by Lateral H₂O Diffusion Into Top-Gate Insulator of a-InGaZnO Thin-Film Transistors. IEEE Journal of the Electron Devices Society, 2022, 10, 341-345.	1.2	11
21	a-IGZO TFTs With Inductively Coupled Plasma Chemical Vapor Deposited SiO_x Gate Dielectric. IEEE Transactions on Electron Devices, 2013, 60, 2687-2690.	1.6	10
22	Scalability and Stability Enhancement in Self-Aligned Top-Gate Indium- Zinc-Oxide TFTs With Al Reacted Source/Drain. IEEE Journal of the Electron Devices Society, 2018, 6, 680-684.	1.2	9
23	Homo-Junction Bottom-Gate Amorphous Inâ€Gaâ€Znâ€O TFTs With Metal-Induced Source/Drain Regions. IEEE Journal of the Electron Devices Society, 2019, 7, 52-56.	1.2	9
24	Manipulation of epsilon-near-zero wavelength for the optimization of linear and nonlinear absorption by supercritical fluid. Scientific Reports, 2021, 11, 15936.	1.6	9
25	Low temperature and high-performance ZnSnO thin-film transistors engineered by <i>in situ</i> thermal manipulation. Journal of Materials Chemistry C, 2022, 10, 3129-3138.	2.7	9
26	A Hybrid a-Si and Poly-Si TFTs Technology for AMOLED Pixel Circuits. Journal of Display Technology, 2014, 10, 317-320.	1.3	8
27	Nonlinear photocurrent-intensity behavior of amorphous InZnO thin film transistors. Applied Physics Letters, 2018, 112, .	1.5	8
28	Unveiling the influence of surrounding materials and realization of multi-level storage in resistive switching memory. Nanoscale, 2020, 12, 22070-22074.	2.8	8
29	Pâ€12: Aâ€Si:H TFT Gate Driver with Shared Dual Pullâ€Down Units for Largeâ€Sized TFTâ€LCD Applications. Digest of Technical Papers SID International Symposium, 2014, 45, 986-989.	0.1	7
30	An Accurate and Fast Current-Biased Voltage-Programmed AMOLED Pixel Circuit With OLED Biased in AC Mode. Journal of Display Technology, 2015, 11, 615-619.	1.3	7
31	P-37: A High Accuracy Current Comparison Scheme for External Compensation Circuit of AMOLED Displays. Digest of Technical Papers SID International Symposium, 2016, 47, 1261-1264.	0.1	7
32	Pâ€9: Parylene / Al₂O₃ Double Layer Passivated Amorphous InGaZnO Thinâ€Film Transistors. Digest of Technical Papers SID International Symposium, 2017, 48, 1258-1261.	0.1	7
33	Floating top gate-induced output enhancement of a-InGaZnO thin film transistors under single gate operations. Applied Physics Letters, 2018, 113, .	1.5	7
34	Self-Heating Stress-Induced Severe Humps in Transfer Characteristics of Amorphous InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2021, 68, 6197-6201.	1.6	7
35	Fabrication of p-type copper oxide thin-film transistors at different oxygen partial pressure. , 2014, , .		6
36	Separate Frame Compensated Current-Biased Voltage-Programmed Active Matrix Organic Light-Emitting Diode Pixel. IEEE Electron Device Letters, 2014, 35, 847-849.	2.2	6

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37	Pâ€48: A Simple Low Temperature Workable aâ€Si:H TFT Integrated Gate Driver on Array. Digest of Technical Papers SID International Symposium, 2015, 46, 1316-1319.	0.1	6
38	Pâ€48: Integrated aâ€IGZO TFT Gate Driver with Programmable Output for AMOLED Display. Digest of Technical Papers SID International Symposium, 2018, 49, 1377-1380.	0.1	6
39	Effects of Ultraviolet Light on the Dual-Sweep I_{DS} & I_{GS} Characteristics of a-InGaZnO ₄ Thin-Film Transistor. IEEE Transactions on Electron Devices, 2019, 66, 1772-1777.	1.6	6
40	Self-Aligned Top-Gate Amorphous Zinc-Tin Oxide Thin-Film Transistor With Source/Drain Regions Doped by Al Reaction. IEEE Journal of the Electron Devices Society, 2021, 9, 653-657.	1.2	6
41	Bifunctional homologous alkali-metal artificial synapse with regenerative ability and mechanism imitation of voltage-gated ion channels. Materials Horizons, 2021, 8, 3072-3081.	6.4	6
42	Roles of Hot Carriers in Dynamic Self-Heating Degradation of a-InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2022, 43, 40-43.	2.2	6
43	Pâ€9: Improved Electrical Stability of Doubleâ€Gate aâ€IGZO TFTs. Digest of Technical Papers SID International Symposium, 2015, 46, 1151-1154.	0.1	5
44	Reliable High-Performance Amorphous InGaZnO Schottky Barrier Diodes With Silicon Dioxide Passivation Layer. IEEE Electron Device Letters, 2021, 42, 1338-1341.	2.2	5
45	A High-Efficiency Segmented Reconfigurable Cyclic Shifter for 5G QC-LDPC Decoder. IEEE Transactions on Circuits and Systems I: Regular Papers, 2022, 69, 401-414.	3.5	5
46	Pâ€28: Robust Gate Driver Design with Etchingâ€Stopâ€Layer Type InGaZnO TFTs Using Stack Buffer Structure. Digest of Technical Papers SID International Symposium, 2017, 48, 1331-1334.	0.1	4
47	Pâ€47: An OLED _S Pixel Circuit with Extended Data Voltage Range for High Resolution Microâ€Displays. Digest of Technical Papers SID International Symposium, 2018, 49, 1373-1376.	0.1	4
48	A Quantum Dot Polarizer for Liquid Crystal Displays With Much Improved Efficiency and Viewing Angle. IEEE Journal of Quantum Electronics, 2019, 55, 1-6.	1.0	4
49	Photovoltage-Coupled Dual-Gate InGaZnO Thin-Film Transistors Operated at the Subthreshold Region for Low-Power Photodetection. ACS Applied Electronic Materials, 2020, 2, 1745-1751.	2.0	4
50	51â€4: QLEDâ€onâ€Silicon Microdisplays. Digest of Technical Papers SID International Symposium, 2020, 51, 758-761.	0.1	4
51	Thorough Elimination of Persistent Photoconduction in Amorphous InZnO Thin-Film Transistor via Dual-Gate Pulses. IEEE Electron Device Letters, 2022, 43, 1247-1250.	2.2	4
52	A Multi- V_{th} a-IGZO TFT Technology Using Anodization to Selectively Reduce Oxygen Vacancy Concentration in Channel Regions. IEEE Electron Device Letters, 2014, 35, 1248-1250.	2.2	3
53	Comparative study of aâ€IGZO TFTs with direct current and radio frequency sputtered channel layers. Journal of the Society for Information Display, 2015, 23, 306-312.	0.8	3
54	Estimation of threshold voltage shift in a-IGZO TFTs under different bias temperature stress by improved stretched-exponential equation. , 2016, , .		3

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55	P454: A High-Voltage Analog Adder Based on Class-B Amplifier for Source Driver of AMOLED External Compensation Scheme. Digest of Technical Papers SID International Symposium, 2017, 48, 1442-1445.	0.1	3
56	P445: Effect of Ar / O ₂ Flow Ratio during Sputtering of InZnO Active Layer on Photocurrent and Responsivity Characteristics of Amorphous InZnO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2020, 51, 1515-1518.	0.1	3
57	152: Student Paper: Programmable LTPS TFT Gate Driver with Tunable Pulse Width for Adjusting AMOLED Brightness. Digest of Technical Papers SID International Symposium, 2021, 52, 180-183.	0.1	3
58	A 16-bit Hybrid ADC with Circular Adder-Based Counting for 15.1μm Pitch 640×512 LWIR FPAs. Chinese Journal of Electronics, 2020, 29, 291-296.	0.7	3
59	Al Reaction-Induced Conductive a-InGaZnO as Pixel Electrode for Active-Matrix Quantum-Dot LED Displays. IEEE Electron Device Letters, 2022, 43, 749-752.	2.2	3
60	Self-Compensation Effect of Photo-Bias Instabilities in a-InGaZnO Thin-Film Transistors Induced by Unique Ion Migration. IEEE Transactions on Electron Devices, 2022, 69, 3206-3212.	1.6	3
61	Effects of over-etching time on the characteristics of amorphous IGZO thin-film transistors with back-channel-etch structure. , 2015, , .		2
62	P41: A Low-Power ESL a-IZGO TFT Integrated Gate Driver Circuit. Digest of Technical Papers SID International Symposium, 2016, 47, 1272-1275.	0.1	2
63	P34: A Peripheral Compensation Scheme for AMOLED with Data Voltage, V _{TH} and Aging Information Analogously Added in Pixel Circuit. Digest of Technical Papers SID International Symposium, 2016, 47, 1250-1253.	0.1	2
64	P15: AZO Etch Buffer Layer based Back-Channel-Etch a-IGZO TFT Technology. Digest of Technical Papers SID International Symposium, 2016, 47, 1172-1175.	0.1	2
65	The design of a 15-inch AMOLED display derived by GOA. , 2018, , .		2
66	P45.2: A gate driver circuit with a-IGZO TFTs for a 15-inch AMOLED display. Digest of Technical Papers SID International Symposium, 2018, 49, 580-583.	0.1	2
67	P46.1: Asymmetric Effects of Gate Bias Stress Voltage on the Stability under Positive and Negative Gate Bias Stress of a-IGZO TFTs. Digest of Technical Papers SID International Symposium, 2018, 49, 597-600.	0.1	2
68	P54: A Low-Power Time-Interleaving Analog Adder for Externally Compensated AMOLED/Micro-LED Displays. Digest of Technical Papers SID International Symposium, 2018, 49, 1399-1402.	0.1	2
69	P1.14: The Influence of Bottom gate Dielectric Roughness on the Performance of Double-Gate a-IGZO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2019, 50, 677-680.	0.1	2
70	P48: A Depletion-Mode Compatible Gate Driver on Array for a-IGZO TFT AMOLED Displays. Digest of Technical Papers SID International Symposium, 2019, 50, 1241-1244.	0.1	2
71	Wafer-Bonding Fabricated CMUT Device with Parylene Coating. Micromachines, 2021, 12, 516.	1.4	2
72	Indium gallium zinc oxide - Carbon nanotube composite thin film transistor. , 2014, , .		1

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73	Magnesium-doped Indium Oxide thin film transistors for ultraviolet detection. , 2014, , .		1
74	Study on the transition between p and n types of SnO _x film deposited by DC sputtering. , 2014, , .		1
75	12-4: TFT Integrated Gate Driver with V _{TH} Shift Compensable Low-Level Holding Unit. Digest of Technical Papers SID International Symposium, 2016, 47, 134-137.	0.1	1
76	Comparison of N ₂ and Ar plasma treatment for source/drain formation in self-aligned top-gate amorphous InGaZnO thin film transistor. , 2016, , .		1
77	Oxygen partial pressure and annealing temperature influence on the performance of back-channel-etch zinc tin oxide thin film transistors. , 2016, , .		1
78	7A3: A Low-Power and High-Stable TFT Gate Driver With a Novel Bootstrap Scheme. Digest of Technical Papers SID International Symposium, 2017, 48, 72-75.	0.1	1
79	8: Photocurrent Characteristics of Amorphous MgInO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2017, 48, 1254-1257.	0.1	1
80	21: The Effect of Thermal Annealing Sequence on the Performance of Self-Aligned Top-Gate aIGZO TFTs. Digest of Technical Papers SID International Symposium, 2017, 48, 1303-1306.	0.1	1
81	A power-on-reset circuit with precisely triggered threshold voltages. , 2017, , .		1
82	P-1.6: Effect of Deposition Condition of Passivation Layer on the Performance of Self-Aligned Top-Gate aIGZO TFTs. Digest of Technical Papers SID International Symposium, 2018, 49, 535-537.	0.1	1
83	Technology Issues for Self-aligned Top-Gate Amorphous Metal Oxide Thin-Film Transistors. , 2018, , .		1
84	1.1: Anomalous Dependence of Threshold Voltage on Channel Width and Drain Voltage in Back-channel-etched aIGZO TFTs. Digest of Technical Papers SID International Symposium, 2018, 49, 516-519.	0.1	1
85	43: Implementation of Digital Thin-Film Transistor Integrated Ambient Light Sensor with High Reliability. Digest of Technical Papers SID International Symposium, 2018, 49, 1357-1360.	0.1	1
86	1.5: Fabrication of Self-Aligned Top-Gate Amorphous InGaZnO Thin-Film Transistors with Submicron Channel Length. Digest of Technical Papers SID International Symposium, 2019, 50, 650-653.	0.1	1
87	108: Oxide Thin Film Transistors Integrated DC-DC Converter with High Efficiency for Passive RFID Tag. Digest of Technical Papers SID International Symposium, 2019, 50, 1660-1663.	0.1	1
88	1.13: The Conductivity Modulation of Amorphous Zinc Tin Oxide Thin Film by aluminum (Al) reaction method. Digest of Technical Papers SID International Symposium, 2019, 50, 673-676.	0.1	1
89	22.2: The influence of Oxygen Partial Pressure on the Performance of back-channel-etched aZTO Thin-Film Transistors. Digest of Technical Papers SID International Symposium, 2019, 50, 216-219.	0.1	1
90	Analysis and improvement of the color anomaly in aSi TFT channel with new 4-mask process. Digest of Technical Papers SID International Symposium, 2020, 51, 51-54.	0.1	1

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91	Pâ€1.14: An aâ€IGZO TFT AMOLED Pixel Circuit with Source Follower Structure to Alleviate Hysteresis Effect. Digest of Technical Papers SID International Symposium, 2021, 52, 448-451.	0.1	1
92	32.3: Integrated Gate Driver Working at Low Temperature for Vehicle Displays. Digest of Technical Papers SID International Symposium, 2021, 52, 200-203.	0.1	1
93	Pâ€1.15: Short time negative gate voltage pulse to eliminate persistent photoconductivity in Amorphous InZnO thin film transistors. Digest of Technical Papers SID International Symposium, 2021, 52, 452-452.	0.1	1
94	Pâ€1.5: <i>Student Poster:</i> Reliable Gate Driver for Realâ€Time External Compensated AMOLED Display Using InGaZnO TFTs. Digest of Technical Papers SID International Symposium, 2021, 52, 1108-1111.	0.1	1
95	Pâ€1.7: Design of AMOLED Pixel Circuit Using LTPO TFTs with Enhanced Reliability. Digest of Technical Papers SID International Symposium, 2021, 52, 1116-1119.	0.1	1
96	Analysis of Carrier Behavior for Amorphous Indium Gallium Zinc Oxide After Supercritical Carbon Dioxide Treatment. Advanced Materials Interfaces, 2022, 9, .	1.9	1
97	P.4: A Chargeâ€Cyclic Digitalâ€toâ€Analog Converter for IGZO TFT Integrated Data Driver. Digest of Technical Papers SID International Symposium, 2013, 44, 999-1002.	0.1	0
98	A gate-stress-induced ΔV<inf>th</inf> model reflecting impact of electric field in IGZO thin film transistors. , 2014, , .		0
99	Development of low temperature amorphous tin-doped indium oxide thin-film transistors technology. , 2014, , .		0
100	Pâ€24: IGZOâ€TFT Based Latch Circuit with High Stability and Fullâ€Swing Output for Systemâ€onâ€Panel^{â€}. Digest of Technical Papers SID International Symposium, 2014, 45, 1031-1034.	0.1	0
101	A concrete integrated gate driver with sharing low-level-holding structure. , 2014, , .		0
102	Homojunction In<inf>2</inf>O<inf>3</inf>-TFTs prepared by anodization technique. , 2014, , .		0
103	Fabrication of indium-tin-oxide thin-film transistor using anodization. , 2014, , .		0
104	Pâ€46: Rowâ€Division Driving Scheme for Active Matrix OLED Displays. Digest of Technical Papers SID International Symposium, 2015, 46, 1308-1311.	0.1	0
105	P-44: A Current Source Free Separate Frame Compensated Voltage-Programmed Active Matrix Organic Light Emitting Diode Pixel Circuit. Digest of Technical Papers SID International Symposium, 2016, 47, 1282-1285.	0.1	0
106	P-36: An Area-Efficient Segmented R-DAC Realized by Low-Voltage Transistors for AMOLED Driver Ics. Digest of Technical Papers SID International Symposium, 2016, 47, 1257-1260.	0.1	0
107	Impact of wet etchant with different PH value on the performance of back-channel-etch a-IGZO thin-film-transistor. , 2016, , .		0
108	Characteristics of amorphous In-Ga-Zn-O thin-film-transistors with channel layer deposited by bias sputtering. , 2016, , .		0

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109	Resistive Random Access Memory: Solving the Scaling Issue of Increasing Forming Voltage in Resistive Random Access Memory Using High-k Spacer Structure (Adv. Electron. Mater. 9/2017). Advanced Electronic Materials, 2017, 3, .	2.6	0
110	TiO ₂ :Nb film thickness influences on the amorphous InGaZnO thin film transistors with Mo/TiO ₂ :Nb source-drain electrodes. , 2017, , .		0
111	A 27.6 MHz 297 μ W 33 ppm/ ^\circ C CMOS relaxation oscillator with an adjustable temperature compensation scheme. , 2017, , .		0
112	Pâ€1.7: Influence of Mg Content and Argon/Oxygen Ratio on Photoelectric properties of coâ€sputtering MIZO. Digest of Technical Papers SID International Symposium, 2018, 49, 538-540.	0.1	0
113	Tunable Manipulation of Microparticles by CMUT. , 2018, , .		0
114	Design of a IGZO TFT-based GOA circuit for external compensation pixel circuits. , 2018, , .		0
115	Optimization of the ZTO/GI interface of Bottom-gate Amorphous ZnSnO Thin-Film Transistor. , 2018, , .		0
116	Ti Film Thickness Influences on the Back Channel Etched Amorphous InGaZnO Thin Film Transistors. , 2018, , .		0
117	Pâ€1.3: The conductivity modulation of amorphous zinc tin oxide thin film by Ar plasma treatment. Digest of Technical Papers SID International Symposium, 2018, 49, 524-527.	0.1	0
118	24.5: Backâ€Channelâ€Etched aâ€IGZO TFTs with TiO ₂ :Nb Protective Layer. Digest of Technical Papers SID International Symposium, 2018, 49, 263-266.	0.1	0
119	Pâ€1.14: The Influence of Dualâ€channel on the Performance of Selfâ€Align Topâ€Gate IGZO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2018, 49, 561-564.	0.1	0
120	1.3: An Evaluation Method of TFT Integrated Gate Driver for UHD Display. Digest of Technical Papers SID International Symposium, 2018, 49, 6-8.	0.1	0
121	Pâ€1.3: Electrical Characteristics and Stability of Doubleâ€Gate aâ€IGZO Thin Film Transistors with Selfâ€Aligned Topâ€Gate. Digest of Technical Papers SID International Symposium, 2018, 49, 1227-1230.	0.1	0
122	Structural, optical and electrical properties of sputtered Nb doped TiO ₂ transparent conductive films. , 2019, , .		0
123	12.5: A Depletionâ€mode Compatible Gate Driver on Array for aâ€IGZO TFTâ€OLED Displays. Digest of Technical Papers SID International Symposium, 2019, 50, 119-121.	0.1	0
124	Pâ€1.11: Relationship between Effective Mobility and Source/Drain Resistance in Selfâ€Aligned Topâ€Gate aâ€IGZO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2019, 50, 666-668.	0.1	0
125	Pâ€76: Origin and Improvement of LCD Reflectivity. Digest of Technical Papers SID International Symposium, 2019, 50, 1522-1525.	0.1	0
126	Pâ€1.7: IGZO TFT Gate Driver with Independent both Bootstrapping and Control Units for AMOLED Mobile Display. Digest of Technical Papers SID International Symposium, 2019, 50, 1275-1278.	0.1	0

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127	Pâ€58: Efficiency Enhancement by Nonâ€Overlapping Time Design and Adaptive Ratio Control for Charge Pump of Display Drivers. Digest of Technical Papers SID International Symposium, 2019, 50, 1452-1455.	0.1	0
128	Pâ€1.7: Selfâ€aligned Topâ€gate aâ€ZrInZnO Thinâ€Film Transistors Fabricated by Cosputtering Technique. Digest of Technical Papers SID International Symposium, 2019, 50, 656-659.	0.1	0
129	Study and reduction of waterfall effect caused by dimming backlight in LCD based on amorphous silicon TFT. Digest of Technical Papers SID International Symposium, 2020, 51, 12-14.	0.1	0
130	Pâ€1.2: A Robust aâ€IGZO TFT Integrated Scan/Emission Driver with Dynamic Inverter for AMOLED Display. Digest of Technical Papers SID International Symposium, 2020, 51, 1354-1357.	0.1	0
131	Performances of Self-Aligned Top-Gate a-IGZO TFTs with Ultrathin PECVD SiO2 Gate Dielectric. , 2020, , .		0
132	Systematic Defect Manipulation in Metal Oxide Semiconductors towards High-Performance Thin-Film Transistors. , 2020, , .		0
133	Eliminating light depolarization from metal microstructure in liquid crystal displays. Journal of the Society for Information Display, 2021, 29, 170-178.	0.8	0
134	High-Speed Low-Power Rail-to-Rail Buffer using Dynamic-Current Feedback for OLED Source Driver Applications. Analog Integrated Circuits and Signal Processing, 0, , 1.	0.9	0
135	Pâ€1.12: Effects of Gate Voltage Pulse Width and Amplitude on Eliminating Persistent Photoconductivity in Amorphous InZnO TFTs. Digest of Technical Papers SID International Symposium, 2021, 52, 703-706.	0.1	0
136	Fully Self-Aligned Homojunction Bottom-Gate Amorphous InGaZnO TFTs with Al Reacted Source/Drain Regions. , 2020, , .		0
137	A Novel Self-Aligned Dopant-Segregated Schottky Tunnel-FET with Asymmetry Sidewall Based on Standard CMOS Technology. , 2020, , .		0